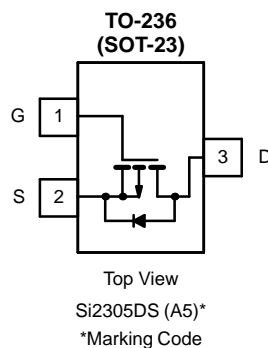




P-Channel 1.25-W, 1.8-V (G-S) MOSFET

TrenchFET[®]
Power MOSFETs
1.8-V Rated

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-8	0.052 @ $V_{GS} = -4.5$ V	± 3.5
	0.071 @ $V_{GS} = -2.5$ V	± 3
	0.108 @ $V_{GS} = -1.8$ V	± 2



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	-8	V
Gate-Source Voltage		V_{GS}	± 8	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	$T_A = 25^\circ\text{C}$	I_D	± 3.5	A
	$T_A = 70^\circ\text{C}$		± 2.8	
Pulsed Drain Current		I_{DM}	± 12	
Continuous Source Current (Diode Conduction) ^{a, b}		I_S	-1.6	
Maximum Power Dissipation ^{a, b}	$T_A = 25^\circ\text{C}$	P_D	1.25	W
	$T_A = 70^\circ\text{C}$		0.8	
Operating Junction and Storage Temperature Range		T_J, T_{Stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}		100	$^\circ\text{C/W}$
	Steady State		130		

Notes

- a. Surface Mounted on FR4 Board.
- b. $t \leq 5$ sec.



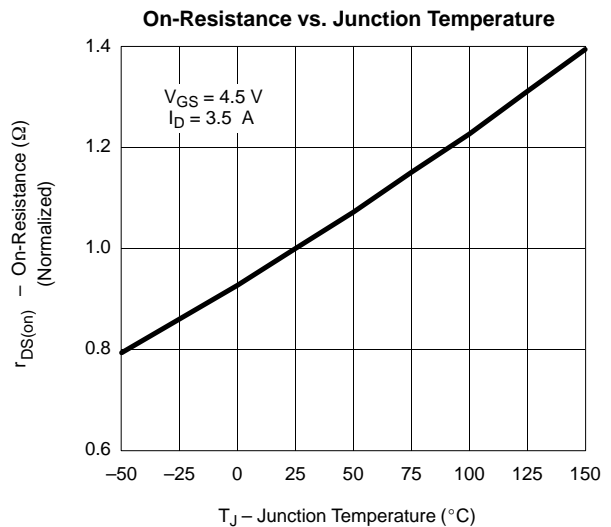
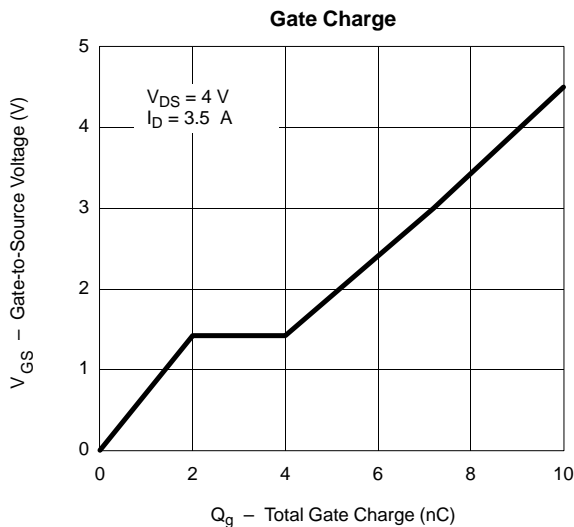
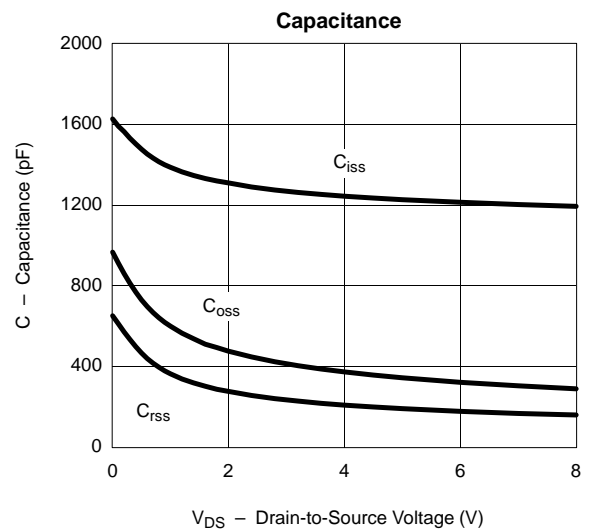
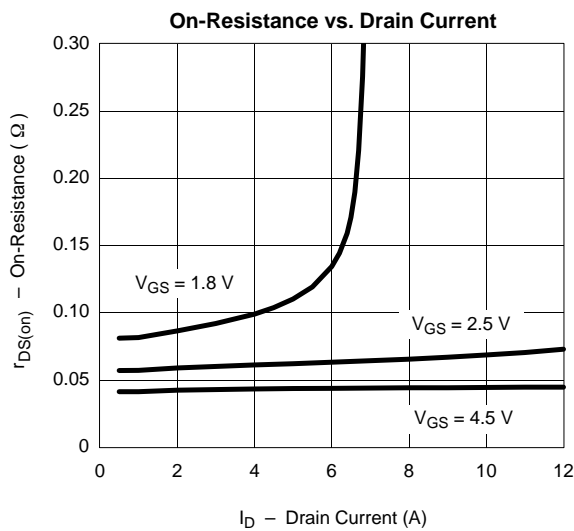
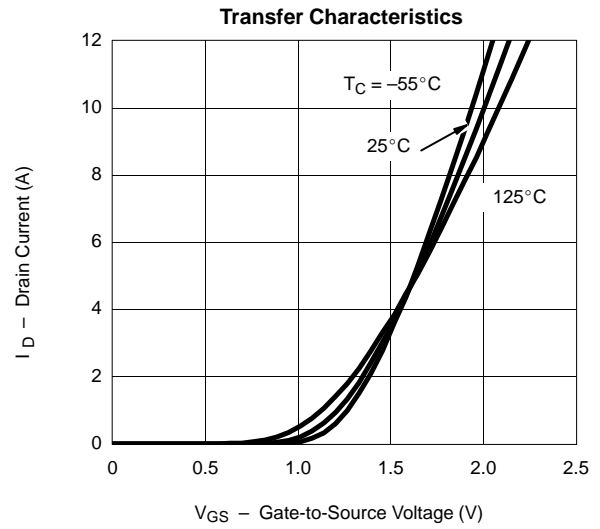
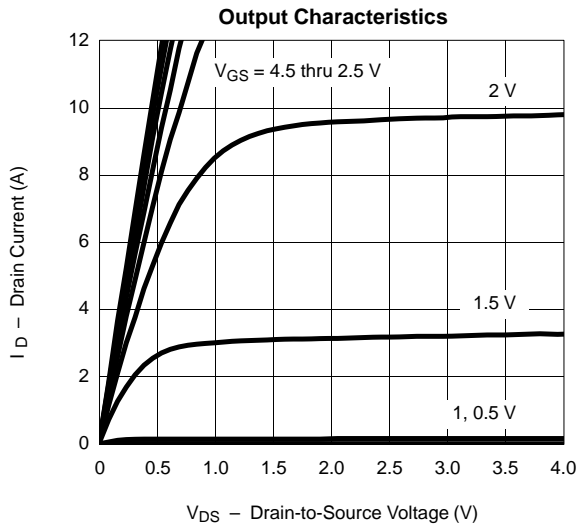
SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = -10 μA	-8			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.45			
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -6.4 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -6.4 V, V _{GS} = 0 V, T _J = 55 °C			-10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ -5 V, V _{GS} = -4.5 V	-6			A
		V _{DS} ≤ -5 V, V _{GS} = -2.5 V	-3			
Drain-Source On-Resistance ^a	r _{DS(on)}	V _{GS} = -4.5 V, I _D = -3.5 A		0.044	0.052	Ω
		V _{GS} = -2.5 V, I _D = -3 A		0.060	0.071	
		V _{GS} = -1.8 V, I _D = -2 A		0.087	0.108	
Forward Transconductance ^a	g _{fs}	V _{DS} = -5 V, I _D = -3.5 A		8.5		S
Diode Forward Voltage	V _{SD}	I _S = -1.6 A, V _{GS} = 0 V			-1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = -4 V, V _{GS} = -4.5 V I _D ≅ -3.5 A		10	15	nC
Gate-Source Charge	Q _{gs}			2		
Gate-Drain Charge	Q _{gd}			2		
Input Capacitance	C _{iss}	V _{DS} = -4 V, V _{GS} = 0, f = 1 MHz		1245		pF
Output Capacitance	C _{oss}			375		
Reverse Transfer Capacitance	C _{rss}			210		
Switching^b						
Turn-On Time	t _{d(on)}	V _{DD} = -4 V, R _L = 4 Ω I _D ≅ -1.0 A, V _{GEN} = -4.5 V R _G = 6 Ω		13	20	ns
	t _r			25	40	
Turn-Off Time	t _{d(off)}			55	80	
	t _f			19	35	

Notes

- a. For DESIGN AID ONLY, not subject to production testing.
- b. Pulse test: PW ≤ 300 μs duty cycle ≤ 2%.
- c. Switching time is essentially independent of operating temperature.



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

